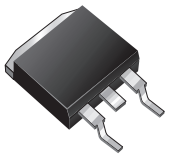
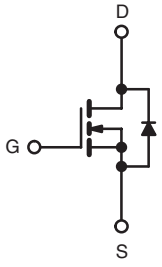
# Power MOSFET

| PRODUCT SUMMARY | | |
|---|---|---|
| $V_{DS}$ (V) | 200 | |
| $R_{DS(on)}$ (Ω) | $V_{GS}$ = 5 V | 0.40 |
| $Q_g$ (Max.) (nC) | 40 | |
| $Q_{gs}$ (nC) | 5.5 | |
| $Q_{gd}$ (nC) | 24 | |
| Configuration | Single | |

**SMD-220**






N-Channel MOSFET

## FEATURES

- Surface Mount
- Available in Tape and Reel
- Dynamic dV/dt Rating
- Repetitive Avalanche Rated
- Logic-Level Gate Drive
- $R_{DS(on)}$ Specified at $V_{GS}$ = 4 V and 5 V
- 150 °C Operating Temperature
- Lead (Pb)-free Available

Available

**RoHS*** COMPLIANT

## DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The SMD-220 is a surface mount power package capable of accommodating die size up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The SMD-220 is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0 W in a typical surface mount application.

| ORDERING INFORMATION | | | |
|---|---|---|---|
| Package | SMD-220 | SMD-220 | SMD-220 |
| Lead (Pb)-free | IRL630SPbF | IRL630STRRPbF[a] | IRL630STRLPbF[a] |
| | SiHL630S-E3 | SiHL630STR-E3[a] | SiHL630STL-E3[a] |
| SnPb | IRL630S | IRL630STRR[a] | IRL630STRL[a] |
| | SiHL630S | SiHL630STR[a] | SiHL630STL[a] |

**Note**

a. See device orientation.

| ABSOLUTE MAXIMUM RATINGS $T_C$ = 25 °C, unless otherwise noted | | | | | |
|---|---|---|---|---|---|
| **PARAMETER** | | | **SYMBOL** | **LIMIT** | **UNIT** |
| Drain-Source Voltage | | | $V_{DS}$ | 200 | V |
| Gate-Source Voltage | | | $V_{GS}$ | ± 10 | |
| Continuous Drain Current | $V_{GS}$ at 5 V | $T_C$ = 25 °C | $I_D$ | 9.0 | A |
| | | $T_C$ = 100 °C | | 5.7 | |
| Pulsed Drain Current[a] | | | $I_{DM}$ | 36 | |
| Linear Derating Factor | | | | 0.59 | W/°C |
| Linear Derating Factor (PCB Mount)[e] | | | | 0.025 | |
| Single Pulse Avalanche Energy[b] | | | $E_{AS}$ | 250 | mJ |
| Avalanche Current[a] | | | $I_{AR}$ | 9.0 | A |
| Repetiitive Avalanche Energy[a] | | | $E_{AR}$ | 7.4 | mJ |
| Maximum Power Dissipation | $T_C$ = 25 °C | | $P_D$ | 74 | W |
| Maximum Power Dissipation (PCB Mount)[e] | $T_A$ = 25 °C | | | 3.1 | |
| Peak Diode Recovery dV/dt[c] | | | dV/dt | 5.0 | V/ns |
| Operating Junction and Storage Temperature Range | | | $T_J$, $T_{stg}$ | - 55 to + 150 | °C |
| Soldering Recommendations (Peak Temperature) | for 10 s | | | 300[d] | |

**Notes**

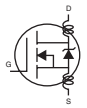
a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. $V_{DD}$ = 25V, starting $T_J$ = 25 °C, L = 4.6 mH, $R_G$ = 25 Ω, $I_{AS}$ = 9.0 A (see fig. 12).
c. $I_{SD}$ ≤ 9.0 A, dI/dt ≤ 120 A/µs, $V_{DD}$ ≤ $V_{DS}$, $T_J$ ≤ 150 °C.
d. 1.6 mm from case.
e. When mounted on 1" square PCB (FR-4 or G-10 material).

* Pb containing terminations are not RoHS compliant, exemptions may apply

| THERMAL RESISTANCE RATINGS | | | | |
|---|---|---|---|---|
| **PARAMETER** | **SYMBOL** | **TYP.** | **MAX.** | **UNIT** |
| Maximum Junction-to-Ambient | $R_{thJA}$ | - | 62 | °C/W |
| Maximum Junction-to-Ambient (PCB Mount)[a] | $R_{thJA}$ | - | 40 | |
| Maximum Junction-to-Case (Drain) | $R_{thJC}$ | - | 1.7 | |

**Note**

a. When mounted on 1" square PCB (FR-4 or G-10 material).

| **SPECIFICATIONS** $T_J$ = 25 °C, unless otherwise noted | | | | | | | |
|---|---|---|---|---|---|---|---|
| **PARAMETER** | **SYMBOL** | **TEST CONDITIONS** | | **MIN.** | **TYP.** | **MAX.** | **UNIT** |
| **Static** | | | | | | | |
| Drain-Source Breakdown Voltage | $V_{DS}$ | $V_{GS}$ = 0 V, $I_D$ = 250 µA | | 200 | - | - | V |
| $V_{DS}$ Temperature Coefficient | $\Delta V_{DS}/T_J$ | Reference to 25 °C, $I_D$ = 1 mA | | - | 0.27 | - | V/°C |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS}$ = $V_{GS}$, $I_D$ = 250 µA | | 1.0 | - | 2.0 | V |
| Gate-Source Leakage | $I_{GSS}$ | $V_{GS}$ = ± 10 V | | - | - | ± 100 | nA |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{DS}$ = 200 V, $V_{GS}$ = 0 V | | - | - | 25 | µA |
| | | $V_{DS}$ = 160 V, $V_{GS}$ = 0 V, $T_J$ = 125 °C | | - | - | 250 | |
| Drain-Source On-State Resistance | $R_{DS(on)}$ | $V_{GS}$ = 5.0 V | $I_D$ = 5.4 A[b] | - | - | 0.40 | Ω |
| | | $V_{GS}$ = 4.0 V | $I_D$ = 4.5 A[b] | - | - | 0.50 | |
| Forward Transconductance | $g_{fs}$ | $V_{DS}$ = 50 V, $I_D$ = 5.4 A[b] | | 4.8 | - | - | S |
| **Dynamic** | | | | | | | |
| Input Capacitance | $C_{iss}$ | $V_{GS}$ = 0 V, $V_{DS}$ = 25 V, f = 1.0 MHz, see fig. 5 | | - | 1100 | - | pF |
| Output Capacitance | $C_{oss}$ | | | - | 220 | - | |
| Reverse Transfer Capacitance | $C_{rss}$ | | | - | 70 | - | |
| Total Gate Charge | $Q_g$ | $V_{GS}$ = 10 V | $I_D$ = 9.0 A, $V_{DS}$ = 160 V, see fig. 6 and 13[b] | - | - | 40 | nC |
| Gate-Source Charge | $Q_{gs}$ | | | - | - | 5.5 | |
| Gate-Drain Charge | $Q_{gd}$ | | | - | - | 24 | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD}$ = 100 V, $I_D$ = 9.0 A, $R_G$ = 6.0 Ω, $R_D$ = 11 Ω, see fig. 10[b] | | - | 8.0 | - | ns |
| Rise Time | $t_r$ | | | - | 57 | - | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | - | 38 | - | |
| Fall Time | $t_f$ | | | - | 33 | - | |
| Internal Drain Inductance | $L_D$ | Between lead, 6 mm (0.25") from package and center of die contact  | | - | 4.5 | - | nH |
| Internal Source Inductance | $L_S$ | | | - | 7.5 | - | |
| **Drain-Source Body Diode Characteristics** | | | | | | | |
| Continuous Source-Drain Diode Current | $I_S$ | MOSFET symbol showing the integral reverse p - n junction diode  | | - | - | 9.0 | A |
| Pulsed Diode Forward Current[a] | $I_{SM}$ | | | - | - | 36 | |
| Body Diode Voltage | $V_{SD}$ | $T_J$ = 25 °C, $I_S$ = 9.0 A, $V_{GS}$ = 0 V[b] | | - | - | 2.0 | V |
| Body Diode Reverse Recovery Time | $t_{rr}$ | $T_J$ = 25 °C, $I_F$ = 9.0 A, dI/dt = 100 A/µs[b] | | - | 230 | 350 | ns |
| Body Diode Reverse Recovery Charge | $Q_{rr}$ | | | - | 1.7 | 2.6 | µC |
| Forward Turn-On Time | $t_{on}$ | Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$) | | | | | |

**Notes**

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).

b. Pulse width ≤ 300 µs; duty cycle ≤ 2 %.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

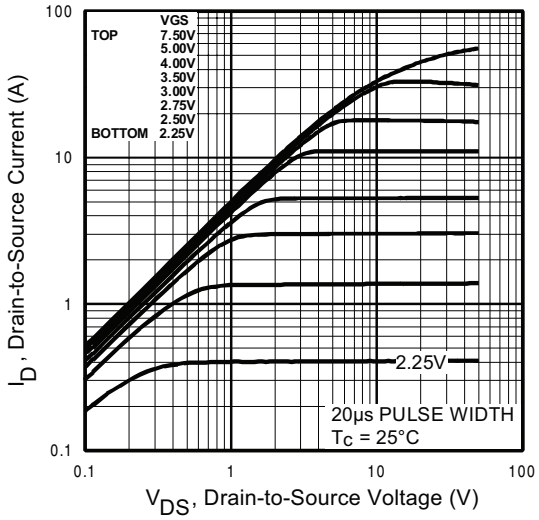



**Fig. 1 - Typical Output Characteristics, $T_C$ = 25 °C**

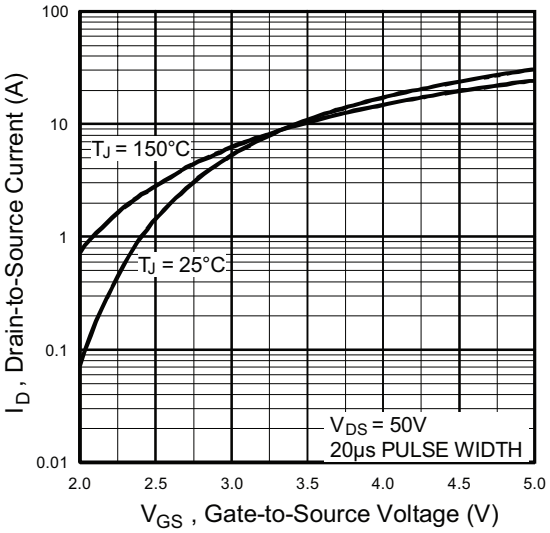



**Fig. 3 - Typical Transfer Characteristics**

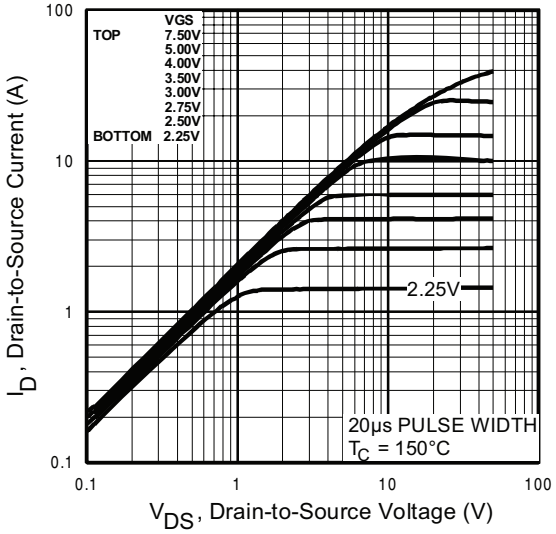



**Fig. 2 - Typical Output Characteristics, $T_C$ = 150 °C**

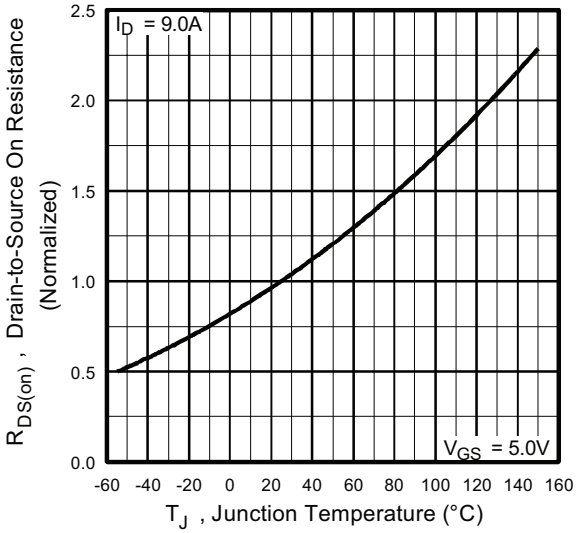



**Fig. 4 - Normalized On-Resistance vs. Temperature**

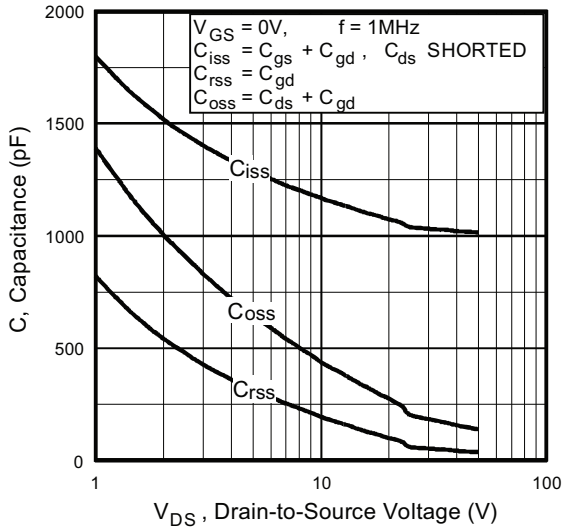



**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**

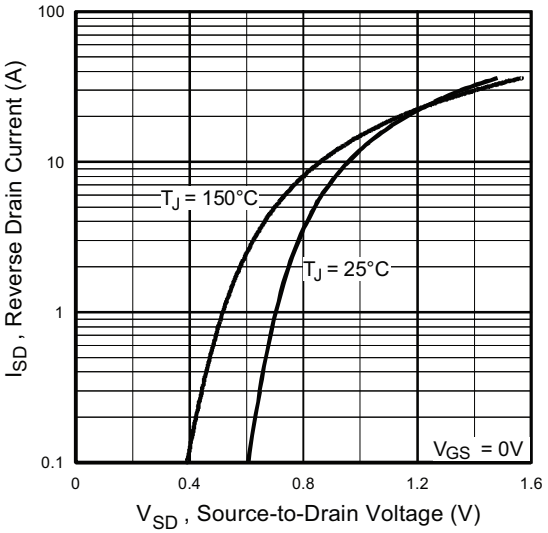



**Fig. 7 - Typical Source-Drain Diode Forward Voltage**

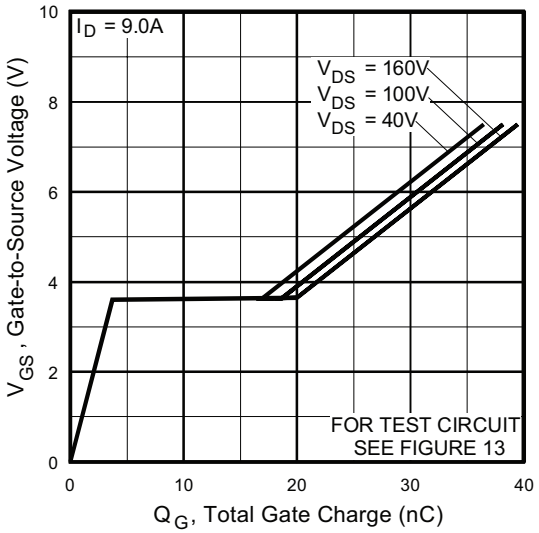



**Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage**

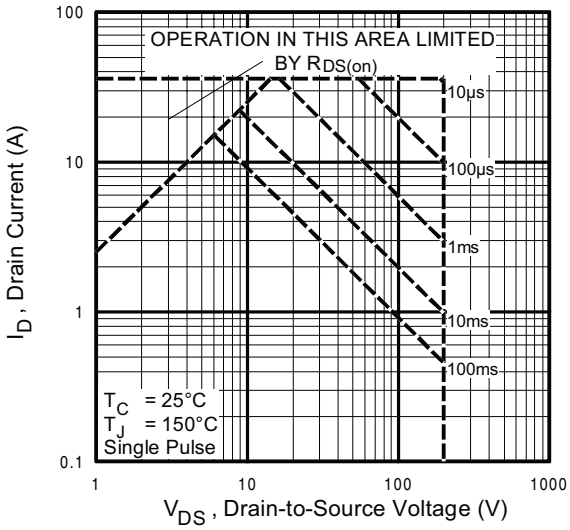



**Fig. 8 - Maximum Safe Operating Area**

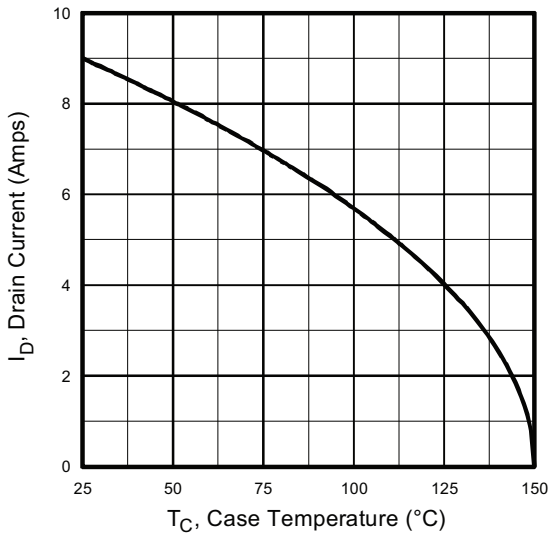



**Fig. 9 - Maximum Drain Current vs. Case Temperature**

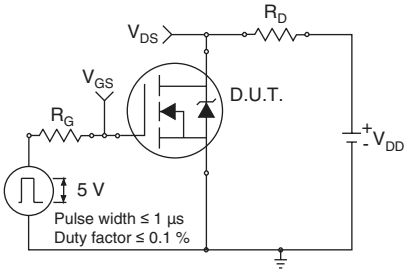



**Fig. 10a - Switching Time Test Circuit**

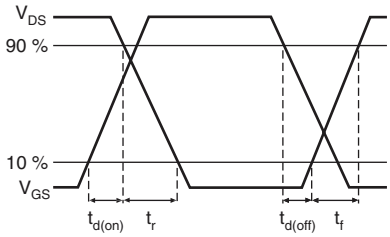



**Fig. 10b - Switching Time Waveforms**

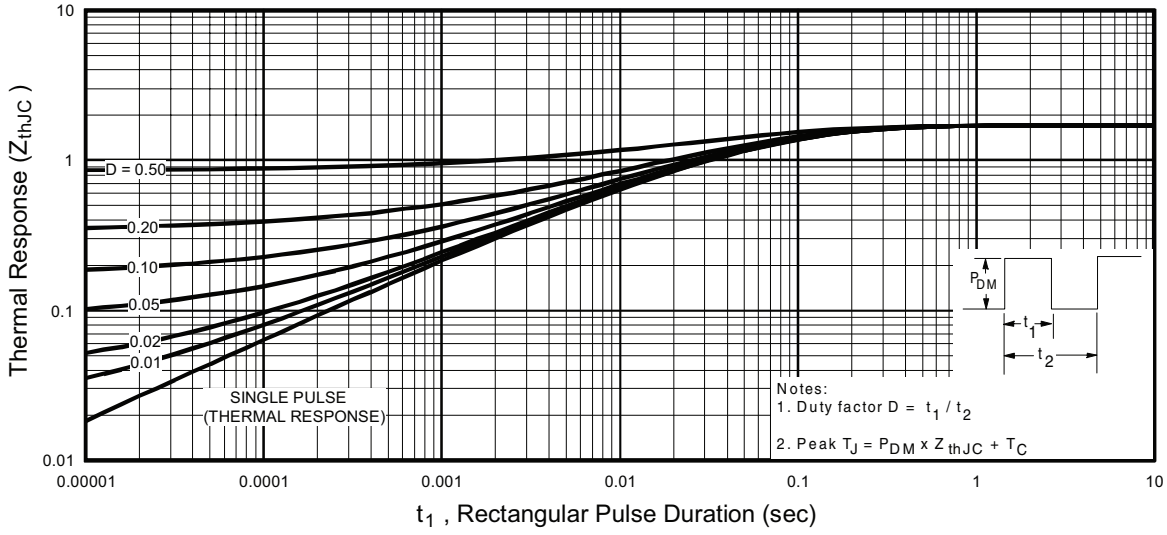



**Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case**

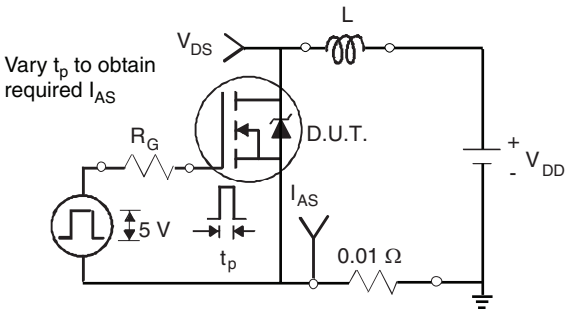



**Fig. 12a - Unclamped Inductive Test Circuit**

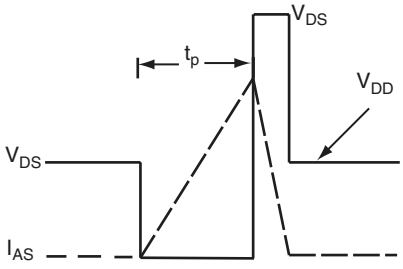



**Fig. 12b - Unclamped Inductive Waveforms**

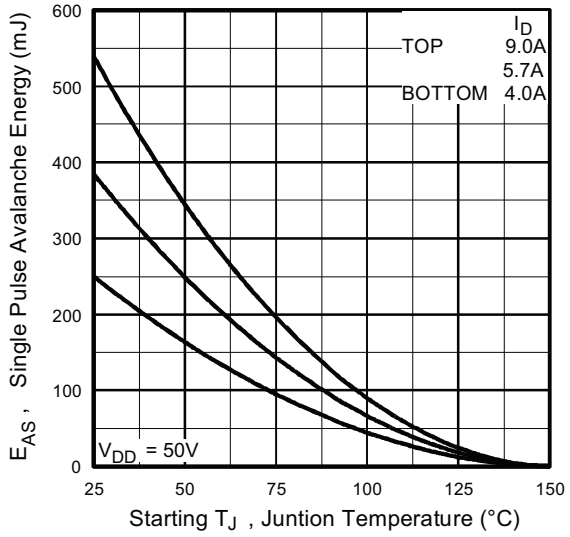



**Fig. 12c - Maximum Avalanche Energy vs. Drain Current**

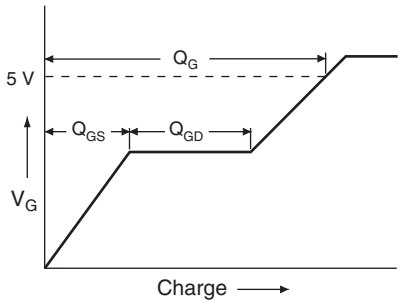



**Fig. 13a - Basic Gate Charge Waveform**

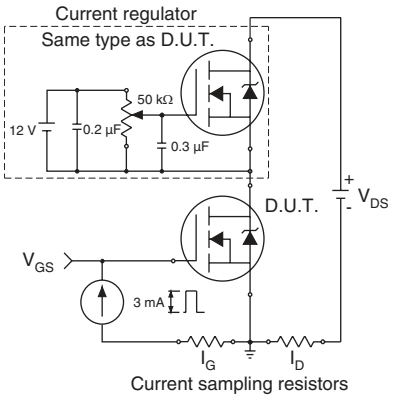
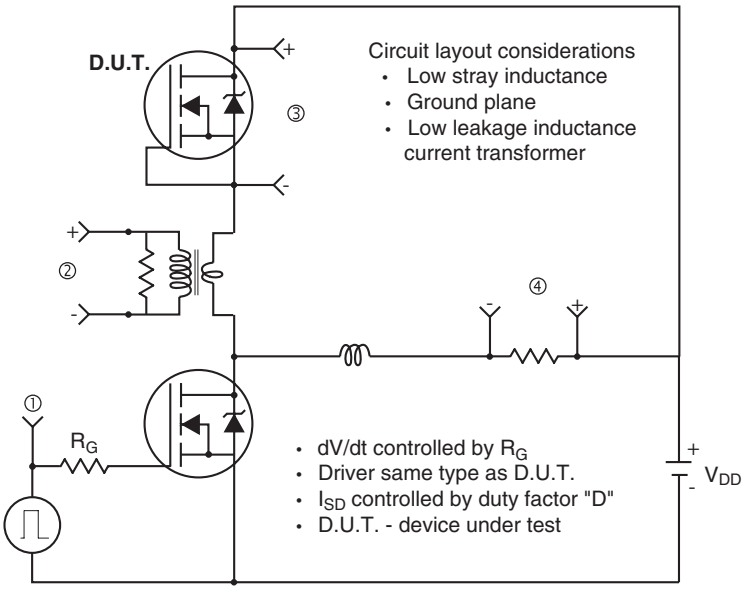
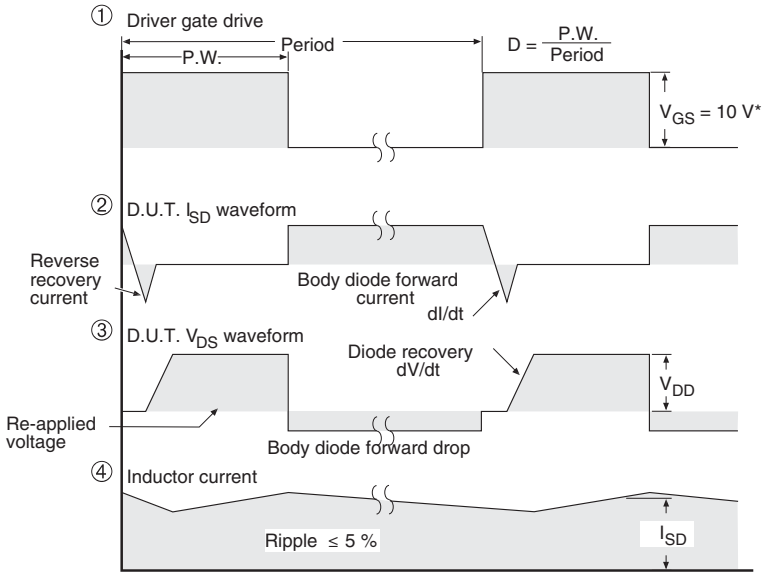



**Fig. 13b - Gate Charge Test Circuit**

## Peak Diode Recovery dV/dt Test Circuit




* $V_{GS}$ = 5 V for logic level devices

**Fig. 14 - For N-Channel**

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